

ABSTRACT

A semiconductor device includes active patterns spaced apart from one another in a first direction and extending in a second direction different from the first direction; a lower channel pattern and a lower source/drain pattern on the active patterns, in which the lower channel pattern and the lower source/drain pattern are alternately arranged in the second direction; an upper channel pattern on the lower channel pattern, and an upper source/drain pattern on the lower source/drain pattern; a gate pattern on the active patterns and on the lower channel pattern and the upper channel pattern; and a gate inner spacer on the gate pattern, and between the lower source/drain pattern and the upper source/drain pattern.

FIG. 1